

Title (en)

METHOD AND APPARATUS FOR THE ETCHING OF PHOTOMASK SUBSTRATES USING PULSED PLASMA

Title (de)

VERFAHREN UND VORRICHTUNG ZUM ÄTZEN VON PHOTOMASKENSUBSTRATEN UNTER VERWENDUNG VON GEPULSTEM PLASMA

Title (fr)

PROCEDE ET APPAREIL D'ATTAQUE DE SUBSTRATS DE MASQUE PHOTOGRAPHIQUE FAISANT APPEL A DU PLASMA PULSE

Publication

EP 1444726 A4 20080813 (EN)

Application

EP 02782196 A 20021022

Priority

- TW 91123170 A 20021008
- US 0233721 W 20021022
- US 34269501 P 20011022
- US 27803502 A 20021022

Abstract (en)

[origin: WO03036704A1] Disclosed is a method and apparatus for the etching of a thin film upon a photomask 24 . The etching is carried out in a reactor 20 via an inductively coupled pulsed plasma. Pulsing of the plasma is achieved by regulating the time period or duty cycle in which the plasma is generated. It has been found that by decreasing the duty cycle, high etch selectively can be achieved and feature sizes can be faithfully maintained.

[origin: WO03036704A1] Disclosed is a method and apparatus for the etching of a thin film upon a photomask (24) . The etching is carried out in a reactor (20) via an inductively coupled pulsed plasma. Pulsing of the plasma is achieved by regulating the time period (or duty cycle) in which the plasma is generated. It has been found that by decreasing the duty cycle, high etch selectively can be achieved and feature sizes can be faithfully maintained.

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H01L 21/302

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CPC (source: EP)

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Citation (search report)

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- [A] WO 9940607 A1 19990812 - LAM RES CORP [US]
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- [A] "RF MODULATION DEVICE AND TECHNIQUE FOR PLASMA PROCESSING AND DIAGNOSTICS", IBM TECHNICAL DISCLOSURE BULLETIN, IBM CORP. NEW YORK, US, vol. 28, no. 4, 1 September 1985 (1985-09-01), pages 1694 - 1696, XP000806378, ISSN: 0018-8689
- See references of WO 03036704A1

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